

Plasmatherm PECVD Tool

- Depositing SiO_2 , SiN_x , *a-Si (dedicated)*
- Samples : Pieces – 8" wafer
- Gases : 10% SiH_4/N_2 ; NH_3 ; N_2O ; N_2
- Min Pressure : 10 mTorr
- Max Temperature : 300 °C

